

DEGRADATION EFFECTS
IN Au–Pt–GaAs SCHOTTKY BARRIER DIODES
INDUCED BY THEIR ACTIVE TREATMENT

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S u m m a r y

The influence of microwave radiation and thermal annealing on the phase-phase interaction at the Pt–GaAs interface and the barrier properties of the junction has been considered. It has been shown that the microwave treatment and the long-term thermal annealing of Au–Pt– n – n^+ –GaAs diode structures with a Schottky barrier can stimulate the degradation of the barrier parameters due to the smearing of the Pt–GaAs interface.